

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
1	BRS	L1	105	hamaguchi near shinichi.in.	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB	2003/09/30 13:58	
2	BRS	L2	1847	yasuda near hiroshi.in.	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB	2003/09/30 13:59	
3	BRS	L3	84	2 and (exposure near apparatus)	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB	2003/09/30 14:00	
4	BRS	L4	123	haraguchi near takeshi.in.	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB	2003/09/30 14:01	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
5	BRS	L5	69	438/463.ccls.	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM-TDB	2003/09/30 14:02	
6	BRS	L6	117415	(expos\$4) near30 (radiat\$3 or irradiat\$3)	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM-TDB	2003/09/30 14:03	
7	BRS	L7	16979	(expos\$4) near20 (wafer or substrate) near30 (radiat\$3 or irradiat\$3)	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM-TDB	2003/09/30 14:03	
8	BRS	L8	1525	(expos\$4) near20 (wafer or substrate) near30 (radiat\$3 or irradiat\$3) near30 (electron near beam\$1)	USPAT; US-PGPUB; ; EPO; JPO; DERWENT; IBM-TDB	2003/09/30 14:09	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
9	BRS	L9	5	(expos\$4) near20 (wafer or substrate) near30 (radiat\$3 or irradiat\$3) near30 (electron near beam\$1) near20 (interval)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/3 0 14:13	
10	BRS	L10	285	(exposure near apparatus) near10 (wafer or substrate) near10 (light near source)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/3 0 14:21	
11	BRS	L11	144	(expos\$3) near10 (wafer or substrate) near10 (light near source) near15 (mov\$3)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/3 0 15:02	
12	BRS	L12	19487	(expos\$3) near30 (electron near beam\$1)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/3 0 15:03	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
13	BRS	L14	5	(expos\$3) near30 (electron near beam\$1) near10 (interval near10 N)	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/3 0 15:03	
14	BRS	L13	100	(expos\$3) near30 (electron near beam\$1) near10 (interval)	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/3 0 15:11	
15	BRS	L16	8	plurality near3 multi near3 electron near lenses	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/3 0 15:12	
16	BRS	L15	157	plurality near3 electron near lenses	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/3 0 16:12	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
17	BRS	L17	655	(electron near lenses) near30 (open43 or aperture\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2003/09/30 16:12	
18	BRS	L18	792	(electron near lenses) near30 (open\$3 or aperture\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2003/09/30 16:13	
19	BRS	L19	13	(electron near lenses) near30 (open\$3 or aperture\$1) near20 (n or interval)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2003/09/30 16:16	
20	BRS	L20	3009	deflector\$1 near15 electron near beams	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB	2003/09/30 16:17	

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments
21	BRS	L21	32	(deflector\$1 near15 electron near beams) near20 (interval)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/09/3 0 16:17	

	U	1	PT	P	Document ID	Issue Date	Pages	Title
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020039829 A1	20020404	12	Semiconductor device manufacturing system and electron beam exposure apparatus
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20010028046 A1	20011011	81	Multi-beam exposure apparatus using a multi-axis electron lens, fabrication method of a semiconductor device
3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20010028044 A1	20011011	81	Multi-beam exposure apparatus using a multi-axis electron lens, electron lens convergencing a plurality of electron beam and fabrication method of a semiconductor device
4	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20010028043 A1	20011011	83	Multi-beam exposure apparatus using a multi-axis electron lens, fabrication method of a multi-axis electron lens and fabrication method of a semiconductor device
5	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20010028042 A1	20011011	82	Multi-beam exposure apparatus using a multi-axis electron lens, electron lens convergencing a plurality of electron beam and fabrication method of a semiconductor device
6	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20010028038 A1	20011011	81	Multi-beam exposure apparatus using a multi-axis electron lens, fabrication method a semiconductor device
7	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 4621215 A	19861104	10	Convergence system for a multi-beam electron gun
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	JP 2002231606 A	20020816	7	ELECTRON BEAM EXPOSURE SYSTEM AND ELECTRON LENS

	U	1	PT	P	Document ID	Issue Date	Pages	Title
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020039829 A1	20020404	12	Semiconductor device manufacturing system and electron beam exposure apparatus
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20010008539 A1	20010719	30	Method of manufacturing a semiconductor optical waveguide array and an array-structured semiconductor optical device
3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6228670 B1	20010508	28	Method of manufacturing a semiconductor optical waveguide array and an array-structured semiconductor optical device
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	JP 04080963 A	19920313	5	SEMICONDUCTOR DEVICE
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020039829 A	20030129	12	Semiconductor device manufacturing system exposes wafer by irradiating several electron beams each having specific interval relative to time interval of wafer movement

	U	1	PT	P	Document ID	Issue Date	Pages	Title
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030155532 A1	20030821	18	Electron-beam lithography
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020039829 A1	20020404	12	Semiconductor device manufacturing system and electron beam exposure apparatus
3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6452320 B1	20020917	14	Lens aperture structure for diminishing focal aberrations in an electron gun
4	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6369512 B1	20020409	10	Dual beam projection tube and electron lens therefor
5	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6133684 A	20001017	9	Electron gun with polygonal shaped rim electrode
6	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 5113112 A	19920512	25	Color cathode ray tube apparatus
7	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 5059858 A	19911022	12	Color cathode ray tube apparatus
8	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 4922166 A	19900501	29	Electron gun for multigun cathode ray tube
9	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 4392914 A	19830712	7	Method for manufacturing mask for color CRT
10	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	JP 03222242 A	19911001	10	COLOR PICTURE TUBE DEVICE
11	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	JP 60218743 A	19851101	4	ELECTRON GUN ELECTRODE STRUCTURE
12	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	EP 424888 A	19910502	25	Colour cathode ray tube apparatus with large aperture lens - has cylindrical 1st electrode allowing beams to pass through and cylindrical electrode holding 1st

	U	1	PT	P	Document ID	Issue Date	Pages	Title
13	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	JP 61263030 A	19861121	NA	Colour TV receiver using one electron gun - has electron lens aperture increased regardless of interval of electron beams formed on deflection surface NoAbstract Dwg 5/5